eformation potentials at L

zation	Zero of d bands above t		
.32 eV	$E_d = 5.75$		
	е		

the relative change of the volume

of ϵ_2 at 4.05 eV, which ilarity of W11+2W12 a changes of M and J while only do not contribute ore, Wij has its maximum and where the contril total ϵ_2 is still small. would have the large contribution of $L_2' \rightarrow L_2'$ es of M and J is justified analysis of the previous the effect of shear strain

L₁ selection rules at re k=L is parallel With spin, these rules w $(|M_{z'}|^2 \ll |M_{x'}|^2)$. The e different from the onn. The strong localization ssures that this deviation of the transition will t ations from the selection

is determined from e ng the assumption di $\partial e = (-9.6 \pm 1.5) \text{ eV}$ and eV for k parallel [111] ese coefficients is due the values given earlier ckground slope used wa used here).

ion Potentials at L

the deformation poten s given earlier12 neglecte the wave function of the tion. The treatment out idization.

niltonian developed by workers,33 and Mueller ce, edited by W. A. Harrisons, Inc., New York, 1960

Phys. Letters 10, 203 (1965) D. Lang, Phys. Rev. 15.

659 (1967).

TABLE VI. Deformation potentials (in eV) of the transitions at L.

reformation cotentials	Experiment		Theory		
	Present paper	Zallen ^a	Present paper	DFJb	Jacobs
$(E_F)/\partial e_{yz}$ $(E_F)/\partial e^{d}$ $(E_F-E_3^u)/\partial e^{d}$	-72 ±12 - 9.6±1.5 - 1.1±0.1	9.7±2.0 Absolute	-56	-5.1 -0.8	
$(L_1 - L_3^u)/\partial e$		value <1.3		-5.9	-4.1

Reference 47.

the form given by Cohen and Mueller.35 Using symetrized plane waves as well as symmetrized tightading functions, we can write down the eigenvalues of and of $L_3^{u,l}$ immediately:

$$L_2' = k^2 - V_{111}, \tag{7}$$

$$L_3^{l,u} = E_d + \pi - \delta \pm \left[(\pi - \delta)^2 + 4.5(-\sigma + \delta)^2 \right]^{1/2}$$
. (8)

The vector k is that of the L point, V111 is a pseudootential form factor, Ed gives the position of the d ands above Γ_1 , and $\sigma \equiv (dd\sigma)$, $\pi \equiv (dd\pi)$, and $\delta \equiv (dd\delta)$ are the two-center tight-binding integrals defined by later and Koster.36 The two L1 levels are obtained om the secular equation

$$\begin{vmatrix} H_{\phi\phi} - E & H_{\phi d} \\ H_{d\phi} & H_{dd} - E \end{vmatrix} = 0.$$
 (9)

The function d is a tight-binding Bloch sum symetrized to L_1 and Φ is a plane wave symmetrized to and orthogonalized to d,

$$\Phi = (\varphi - b_d d)/C. \tag{10}$$

the abbreviations used in Eq. (10) are

$$\varphi = (2/V)^{1/2} \cos(\mathbf{k} \cdot \mathbf{r}), \tag{11}$$

$$b_d = \langle \varphi | d \rangle, \tag{12}$$

$$C^2 = 1 - b_d^2. (13)$$

The matrix elements of Eq. (9) are

$$H_{dd} = E_d - 4(\pi - \delta), \tag{14}$$

$$H_{\Phi d} = (H_{\omega d} - b_d H_{dd})/C, \tag{15}$$

$$H_{\Phi\Phi} = (k^2 + V_{111} + V_{\varphi\varphi}^{(2)} + b_d^2 H_{dd} - 2b_d H_{\varphi d})/C^2$$
. (16)

We calculated bd and the tight-binding integrals using the atomic wave function and the atomic potential alculated by Hartree and Hartree³⁷ and parametrized

hio, 1967), p. 61.

J. C. Slater and G. F. Koster, Phys. Rev. 94, 1498 (1954).

D. R. Hartree and W. Hartree, Proc. Roy. Soc. (London) 4157, 490 (1936).

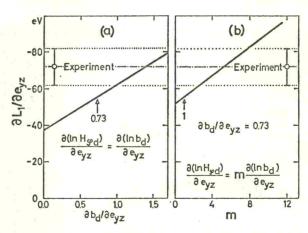


Fig. 13. The dependence of the shear strain deformation potential $\partial L_1/\partial e_{yz}$ on the strain coefficient of the orthogonality integral b_d [part (a) of the figure] and on the strain coefficient of the hybridization $H_{\varphi d}$ [part (b) of the figure]. The value $\partial b_d/\partial e_{yz} = 0.73$ was calculated using atomic d functions.

by Fletcher and Wohlfahrth. 38 The numerical values are given in Table V. The tight binding integrals agree with those calculated by Fletcher and Wohlfahrth. The value of the orthogonalization integral b_d given by Mueller³⁴ is 16% lower than the one reported here.

A first-principles calculation of the quantities E_d , $H_{\varphi d}$, and $\Delta V_{\varphi \varphi}^{(2)}$ is extremely difficult and will not be attempted here. Instead, we determine them from the eigenvalues of Fig. 9,13,14 using the calculated values of b_d and of the tight-binding integrals. In particular, the value of the hybridization integral $H_{\varphi d}$ is evaluated from the difference between H_{dd} (the eigenvalue of L_1^d , neglecting hybridization) and L1d. Ed is calculated from $L_3-\Gamma_1$ using Eq. (8). $(L_3^u-L_3^l)$ given by this equation agrees with the value taken from Fig. 9. One would expect this, since these bands have no interaction with the sp bands.) The form factor V_{111} given by Eq. (7) is also taken from the calculated band structure.

 $\Delta V_{\varphi\varphi}^{(2)}$ is the matrix element of the crystal potential, calculated with the l=2 component of φ . It was introduced in the model Hamiltonian35 following a suggestion by Heine. 39 Its numerical value (calculated using the $L_1 - L_1^d$ gap of Fig. 9) is small, namely, -0.75 eV. Neglecting $\Delta V_{\varphi\varphi}^{(2)}$ gives $L_1 - L_1^d = 9.85$ eV using Eq. (9), which is only 0.60 eV higher than the value of Fig. 9. $\Delta V_{\varphi\varphi}^{(2)}$ will be neglected in the following. The zero-strain values of V_{111} , $H_{\varphi d}$, and E_d are listed in Table V.

The tight-binding parameters for changed nearestneighbor distances were calculated in the same way as for the distance in the unstrained crystal. For trigonal distortion (Table I) and levels with k parallel to [111], the strain coefficient of H_{dd} is (R is the nearest-neighbor

Reference 48. Reference 48. It is the relative change of the volume V.

¹⁴ M. H. Cohen and F. M. Mueller, in Atomic and Electronic fructure of Metals (American Society for Metals, Metals Park,

³⁸ G. C. Fletcher and E. P. Wohlfahrth, Phil. Mag. 42, 106 (1951)

³⁹ V. Heine, Phys. Rev. 153, 673 (1967).